ABSTRACT OF THE DISCLOSURE

On a GaAs substrate (1), are formed a DBR (Distributed Bragg Reflector) (3), and a light-emitting layer (5) made of a plurality of layers of $Al_yGa_zIn_{1-y-z}P$ ($0 \leq y \leq 1$, $0 \leq z \leq 1$) above the DBR (3). A semiconductor layer or a plurality of semiconductor layers (6) - (10) having a number of layers of 1 or more are formed on the light-emitting layer (5), and a grating pattern for scattering light is formed on a surface of the semiconductor layer (9) by photolithography and by etching with a sulfuric acid/hydrogen peroxide based etchant. Thus, a semiconductor device small in radiation angle dependence of light emission wavelength, as well as a manufacturing method therefor, are provided.